

General Description

The MY3400 is the high cell density trenched N-CH MOSFET, which provides excellent $R_{DS(ON)}$ and efficiency for most of the small power switching and load switch applications.

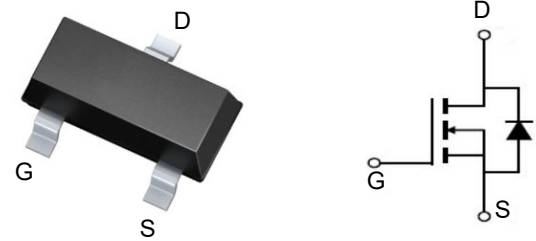


Features

V_{DSS}	20	V
I_D	3	A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	35	m Ω
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	42	m Ω

Application

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY3400	SOT-23	A09T	3000

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	3.0	A
Drain Current-Pulsed (Note 1)	I_{DM}	12	A
Maximum Power Dissipation	P_D	0.8	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	156	$^{\circ}C/W$

Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA

Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	0.75	1.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =2.8A	-	42	80	mΩ
		V _{GS} =4.5V, I _D =3A	-	35	50	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V F=1.0MHz	-	240	-	PF
Output Capacitance	C _{oss}		-	45	-	PF
Reverse Transfer Capacitance	C _{rss}		-	23	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V, R _L =3.3Ω V _{GS} =4.5V, R _{GEN} =6Ω	-	2.3	-	nS
Turn-on Rise Time	t _r		-	3.1	-	nS
Turn-Off Delay Time	t _{d(off)}		-	20	-	nS
Turn-Off Fall Time	t _f		-	2.5	-	nS
Total Gate Charge	Q _g	V _{DS} =10V, I _D =3A V _{GS} =4.5V	-	2.7	5	nC
Gate-Source Charge	Q _{gs}		-	0.4	-	nC
Gate-Drain Charge	Q _{gd}		-	0.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

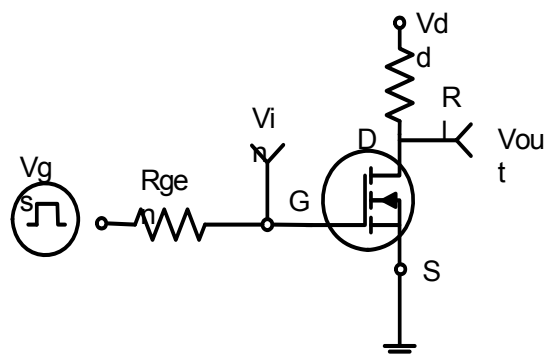


Figure 1: Switching Test Circuit

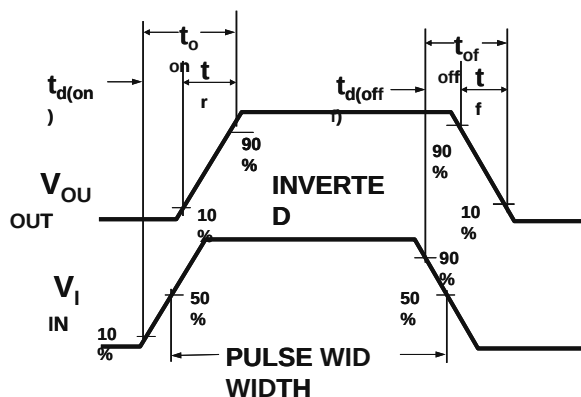


Figure 2: Switching Waveforms

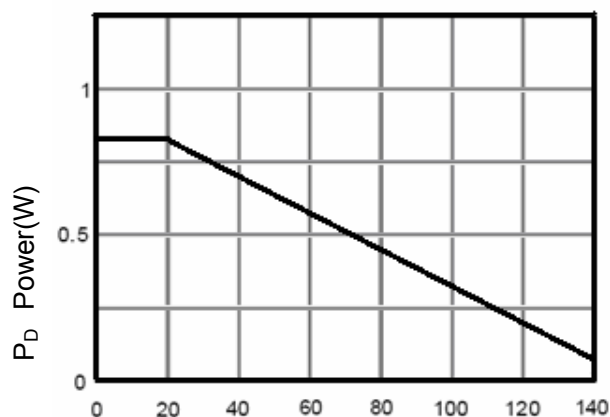


Figure 3 Power Dissipation

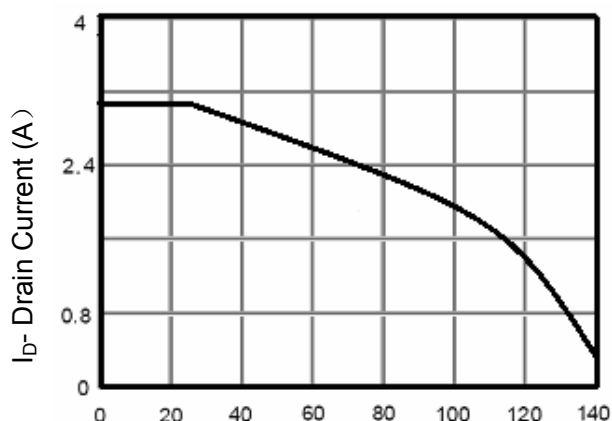


Figure 4 Drain Current

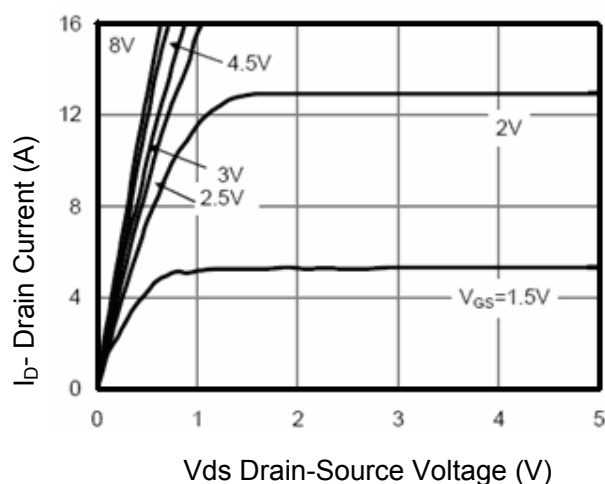


Figure 5 Output Characteristics

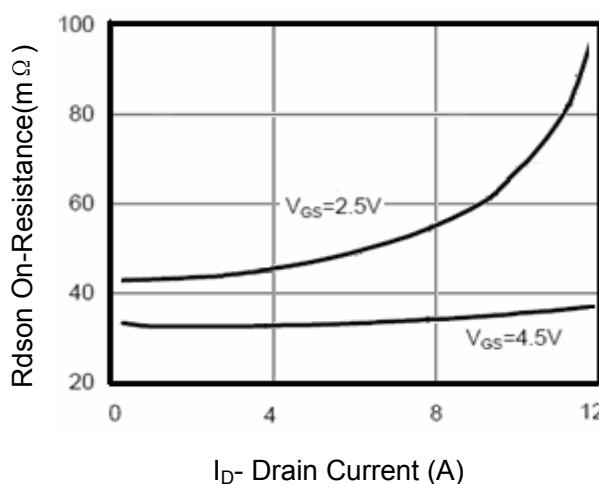


Figure 6 Drain-Source On-Resistance

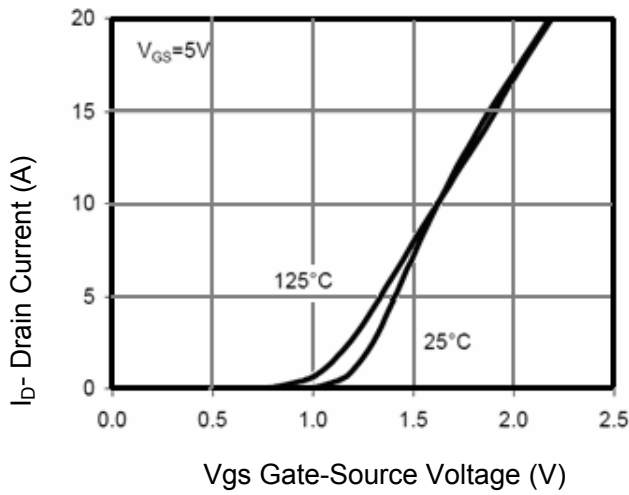


Figure 7 Transfer Characteristics

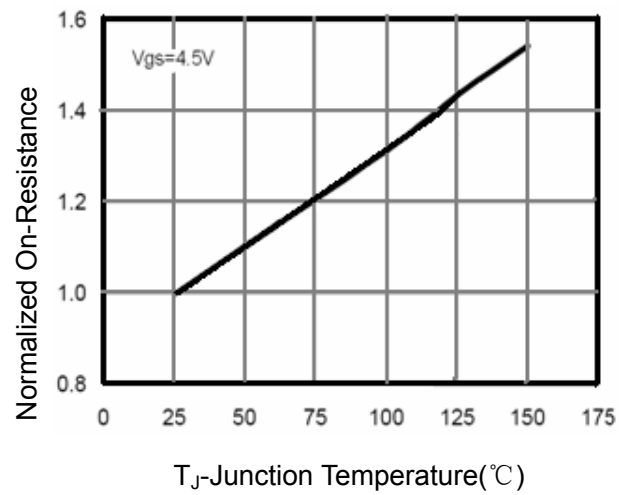


Figure 8 Drain-Source On-Resistance

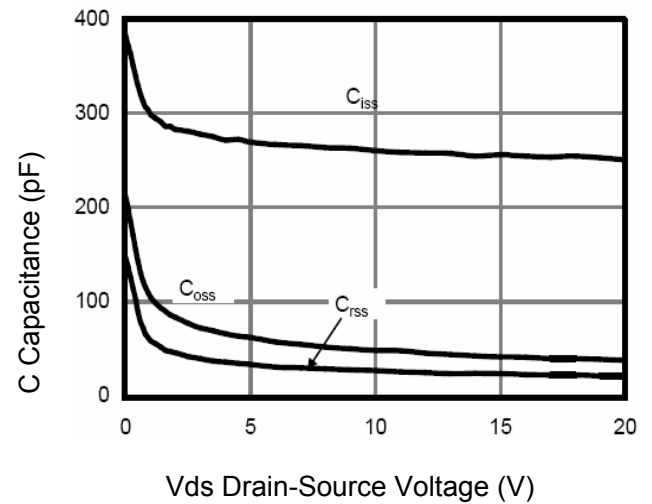
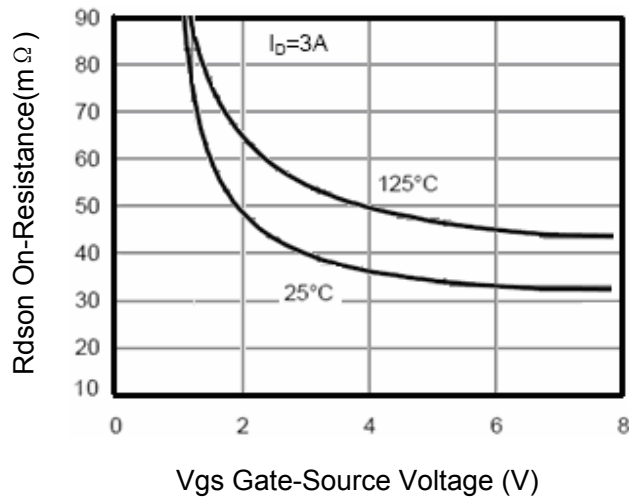


Figure 10 Capacitance vs Vds

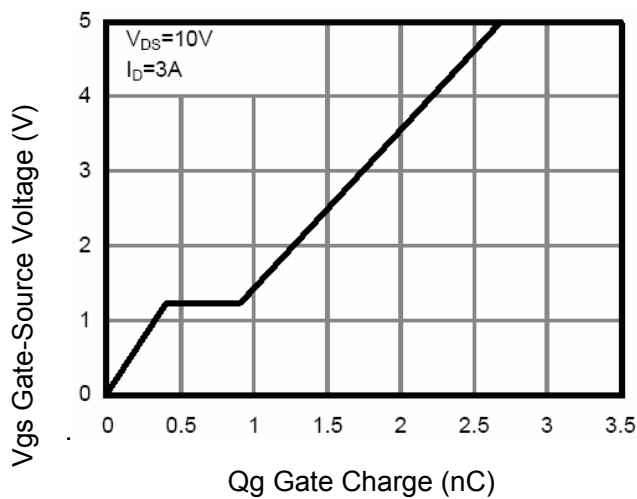


Figure 11 Gate Charge

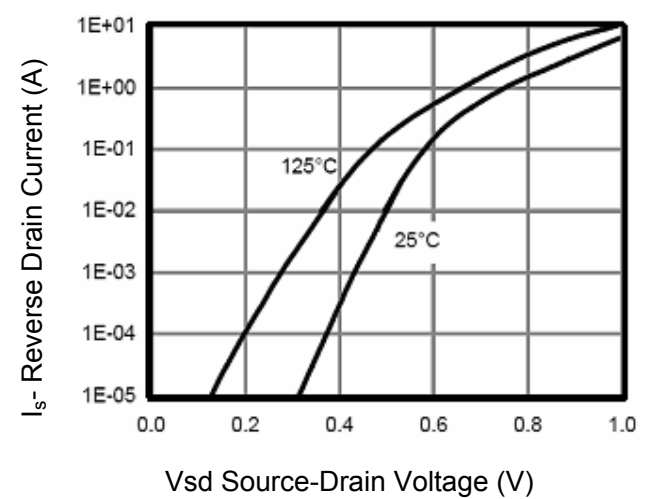
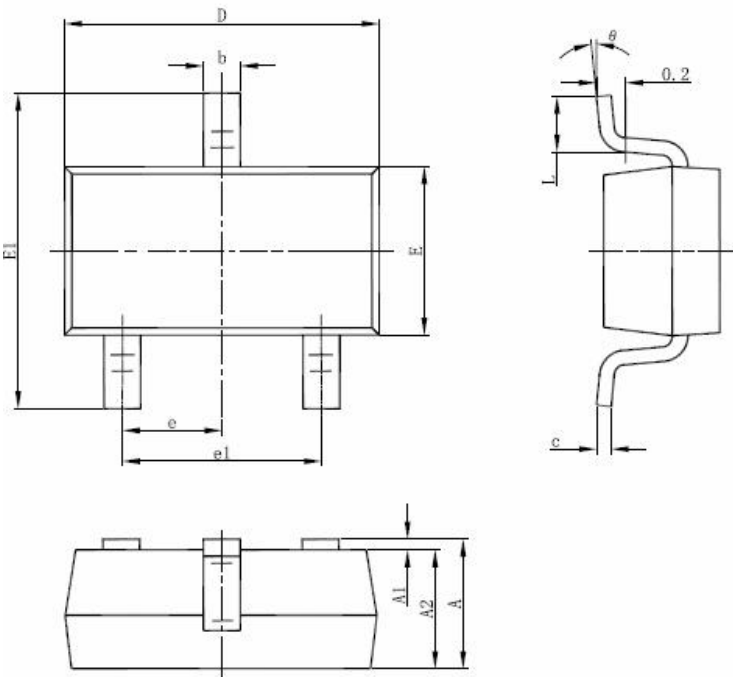


Figure 12 Source- Drain Diode Forward

Package Mechanical Data-SOT-23



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°